

2 Please amend Claim 34, as follows: }

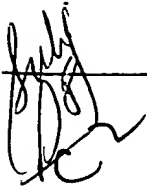
34. (Twice Amended) A semiconductor device, comprising:

- a substrate;
- a gate electrode provided on said substrate;
- a diffusion region formed in said substrate adjacent to said gate electrode;
- a side-wall insulation film formed on side wall of said gate electrode; [and]
- a self-aligned contact hole defined by said side-wall oxide film and exposing said diffusion region; and

a silicide region formed selectively on a surface of said diffusion region,

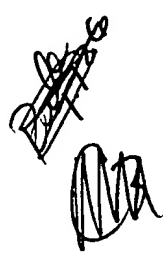
wherein said semiconductor device further includes:

- a first insulation film provided on said gate electrode so as to cover said side wall oxide film partially;
- a second insulation film having a composition different from a composition of said first insulation film and provided on said first insulation film;
- an interlayer insulation film deposited on said second insulation film;
- a contact hole formed in said interlayer insulation film, said contact hole extending through said first and second insulation films and exposing said self-aligned contact hole;
- said first insulation film is formed of PSG containing P with an amount of about 6 wt% or less.

 Please amend Claim 41, as follows:

41. (Twice Amended) A semiconductor device as claimed in claim [40] 38, further comprising another silicide region formed selectively on a surface of said gate electrode.

Add new Claim 42, as follows:

-  ~~43~~ ~~42.~~ A method of fabricating a semiconductor device, comprising the steps of:
- (A) forming a refractory metal layer on a diffusion region in a semiconductor substrate;
  - (B) forming a self-aligned silicide layer on said refractory metal layer by applying a heat-treatment process;
  - (C) forming an insulation film on a surface of said silicide layer by conducting a plasma CVD process while using a source gas containing  $\text{SiH}_4$  and  $\text{N}_2\text{O}$  with a ratio of  $\text{N}_2\text{O}$  with respect to  $\text{SiH}_4$  equal to or less than 5;
  - (D) forming a nitride film, after said step (C), on said insulation film in contact with said insulation film, without exposing a surface of said insulation film to the air;
  - (E) forming an interlayer insulation film so as to cover said nitride film; and
  - (F) forming a window exposing said silicide layer, by applying a dry etching process consecutively to said interlayer insulation film, said nitride film, and said insulation film.

Cancel Claim 40, without prejudice or disclaimer.